# **MC74HCT573A**

## Octal 3-State Noninverting Transparent Latch with LSTTL Compatible Inputs

## High–Performance Silicon–Gate CMOS

The MC74HCT573A is identical in pinout to the LS573. This device may be used as a level converter for interfacing TTL or NMOS outputs to High–Speed CMOS inputs.

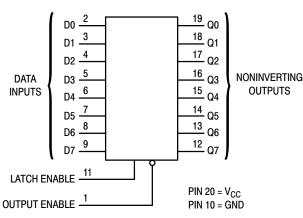
These latches appear transparent to data (i.e., the outputs change asynchronously) when Latch Enable is high. When Latch Enable goes low, data meeting the setup and hold times becomes latched.

The Output Enable input does not affect the state of the latches, but when Output Enable is high, all device outputs are forced to the high–impedance state. Thus, data may be latched even when the outputs are not enabled.

The HCT573A is identical in function to the HCT373A but has the Data Inputs on the opposite side of the package from the outputs to facilitate PC board layout.

#### Features

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS–Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 10 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 234 FETs or 58.5 Equivalent Gates
  - Improved Propagation Delays
  - ♦ 50% Lower Quiescent Power
- These Devices are Pb-Free and are RoHS Compliant



#### LOGIC DIAGRAM



## **ON Semiconductor**

http://onsemi.com



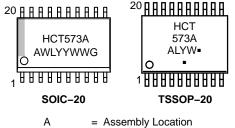
DW SUFFIX CASE 751D

TSSOP-20 DT SUFFIX CASE 948E

#### PIN ASSIGNMENT

OUTPUT			
ENABLE D	1.	20 🛓	V <sub>CC</sub>
D0 🛛	2	19 🗅	Q0
D1 🛛	3	18 🛓	Q1
D2 🗆	4	17 þ	Q2
D3 🗆	5	16 🗅	Q3
D4 🛛	6	15 🗅	Q4
D5 🗆	7	14 🛓	Q5
D6 🗆	8	13 🛓	Q6
D7 🗆	9	12 🛓	Q7
GND 🗆	10	11 þ	LATCH
			ENABLE

#### MARKING DIAGRAMS



= Assembly Location

WL, L = Wafe YY, Y = Year

- WW, W = Work Week
- G or = = Pb–Free Package

(Note: Microdot may be in either location)

Device	Package	Shipping <sup>†</sup>
MC74HCT573ADWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MC74HCT573ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

<sup>+</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### FUNCTION TABLE

Inputs			Output
Output Enable	Latch Enable	D	Q
L	Н	Н	Н
L	Н	L	L
L	L	X	No Change
Н	Х	X	Z

X = Don't Care

Z = High Impedance

Design Criteria	Value	Units
Internal Gate Count*	58.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рJ

\*Equivalent to a two-input NAND gate.

#### MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
Vout	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
PD	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds (TSSOP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

TSSOP Package: -6.1 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	T <sub>A</sub> Operating Temperature, All Package Types		+125	°C
t <sub>r</sub> , t <sub>f</sub>	t <sub>r</sub> , t <sub>f</sub> Input Rise and Fall Time (Figure 1)		500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## **MC74HCT573A**

				Gu	aranteed Li	imit	
Symbol	Parameter	Test Conditions	v <sub>cc</sub> v	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High–Level Input Voltage	$\begin{array}{l} V_{out} = 0.1 \ V \ or \ V_{CC} - 0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$\begin{array}{l} V_{out} = 0.1 \ V \ or \ V_{CC} - 0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V <sub>OH</sub>	Minimum High–Level Output Voltage		4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
			4.5	3.98	3.84	3.7	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$ \begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\  I_{out}  &\leq 20 \ \mu A \end{aligned} $	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μA
I <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5	±0.5	±5.0	±10	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$\label{eq:Vin} \begin{array}{l} V_{in} = V_{CC} \text{ or } GND \\ I_{out} \leq 0 \ \mu A \end{array}$	5.5	4.0	40	160	μA
$\Delta I_{CC}$	Additional Quiescent Supply Current	$V_{in} = 2.4$ V, Any One Input $V_{in} = V_{CC}$ or GND, Other Inputs		≥-55°C	25°C to	o 125°C	
		$V_{in} = V_{CC}$ of GND, other inputs $I_{out} = 0 \ \mu A$	5.5	2.9	2	.4	mA

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

## AC ELECTRICAL CHARACTERISTICS (V\_{CC} = 5.0 V $\pm 10\%, \, C_L$ = 50 pF, Input $t_f$ = $t_f$ = 6.0 ns)

		G	Guaranteed Limit			
Symbol	Parameter	–55 to 25°C	≤ 85°C	≤ 125°C	Unit	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input D to Output Q (Figures 1 and 5)	30	38	45	ns	
t <sub>PLH</sub> t <sub>PHL</sub>	Maximum Propagation Delay, Latch Enable to Q (Figures 2 and 5)	30	38	45	ns	
T <sub>PLZ,</sub> T <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	28	35	42	ns	
t <sub>TZL,</sub> t <sub>TZH</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	28	35	42	ns	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, any Output (Figures 1 and 5)	12	15	18	ns	
C <sub>in</sub>	Maximum Input Capacitance	10	10	10	pF	
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High–Impedance State)	15	15	15	pF	
i		Туріс	al @ 25°C, V	<sub>CC</sub> = 5.0 V	1	

 $C_{PD}$  Power Dissipation Capacitance (Per Enabled Output)\*

 \* Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .
 48

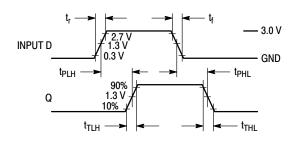
### **TIMING REQUIREMENTS** (V<sub>CC</sub> = 5.0 V $\pm$ 10%, C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6.0 ns)

			Guaranteed Limit								
			–55 to 25°C		-55 to 25°C ≤ 8		-55 to 25°C ≤ 85°C		≤ <b>12</b>	5°C	
Symbol	Parameter	Fig.	Min	Max	Min	Max	Min	Max	Unit		
t <sub>su</sub>	Minimum Setup Time, Input D to Latch Enable	4	10		13		15		ns		
t <sub>h</sub>	Minimum Hold Time, Latch Enable to Input D	4 5.0			5.0		5.0		ns		
tw	Minimum Pulse Width, Latch Enable	2 15		19		22		ns			
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times	1		500		500		500	ns		

pF

## **MC74HCT573A**

### SWITCHING WAVEFORMS





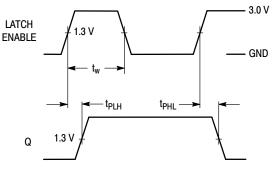


Figure 2.

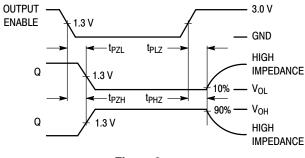
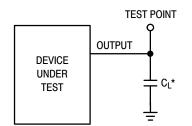
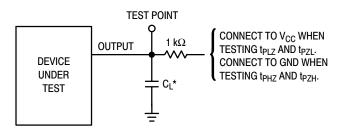


Figure 3.



\*Includes all probe and jig capacitance

Figure 5. Test Circuit



\*Includes all probe and jig capacitance



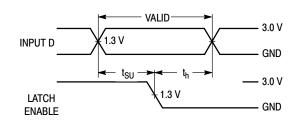
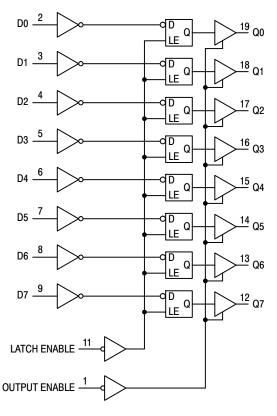


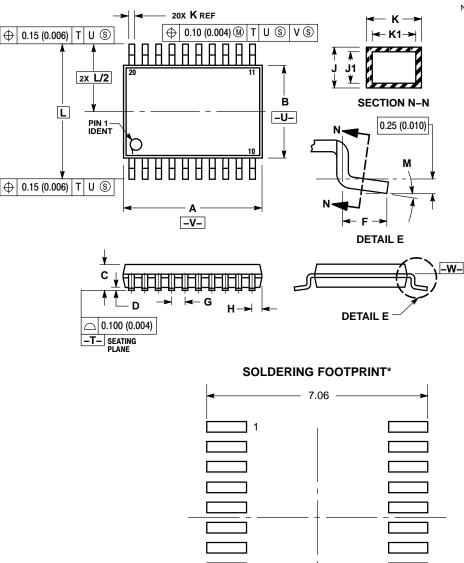
Figure 4.



## EXPANDED LOGIC DIAGRAM

#### PACKAGE DIMENSIONS

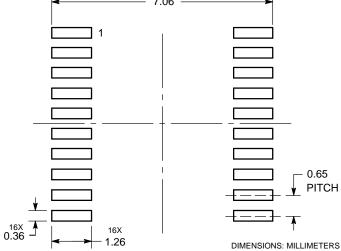
TSSOP-20 DT SUFFIX CASE 948E-02 **ISSUE C** 

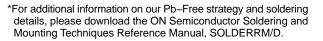


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEA 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

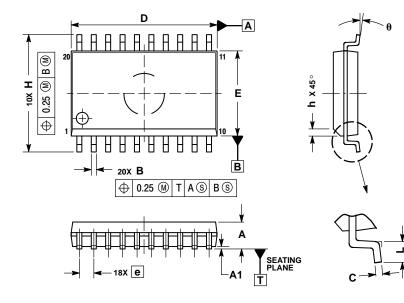
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007 0.01		
L	6.40		0.252 BSC		
М	0°	8°	0° 8°		





#### PACKAGE DIMENSIONS

SOIC-20 DW SUFFIX CASE 751D-05 ISSUE G



NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
   DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
C	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

ON Semiconductor and the 🛄 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC for any such unintended or unauthorized application, Buyer shall indemnity and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the des

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative